Dr. Avraham Publications:

1. A. Karsenty and **A. Chelly**, "Y-Function Analysis of the Low Temperature Behavior of Ultrathin Film FD SOI MOSFETs," Active and Passive Electronic Components, vol. 2014, Article ID 697369, 10 pages, 2014.
2. A. Karsenty and **A. Chelly**, "Application, Modeling and Limitations of Y-function based Methods for Massive Series Resistance in Nanoscale SOI MOSFETs", Solid State Electronics, Volume 92, February 2014, Pages 12–19.
3. A. Karsenty and **A. Chelly**, "Comparative study of NSB and UTB SOI MOSFETs Characteristics by Extraction of Series Resistance", Solid State Electronics, Volume 91, January 2014, pages 28-35.
4. M. Shviro, A. Paszternák, **A. Chelly** and D. Zitoun, "Zigzag-shaped nickel nanowires via organometallic template-free route", Journal of Nanoparticle Research, Volume 15, Issue 8, August 2013, Pages 1-10.
5. S. Levy, I. Shlimak, **A. Chelly** and, Z. Zalevsky "C-V characteristics of Si-MOS structures with Ge nanocrystals", 21st Int. Symp. "Nanostructures: Physics and Technology" St. Petersburg, Russia, June 24-28, 2013.
6. A. Karsenty and **A. Chelly** "Modeling of the channel thickness influence on electrical characteristics and series resistance in gate-recessed nanoscale SOI MOSFETs" Active and Passive Electronic Components, Volume 2013, 2013.
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8. A. Karsenty and **A. Chelly**, "A Comparative Study of Electrical Transport Phenomena in Ultrathin vs. Nanoscale SOI MOSFETs Devices", International Journal of Electrical Science and Engineering Vol:7 No:1, 1243-1247 (2013).
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15. T.Angot, **R.Chelly** "Stable Ge-H phase at 620 K on Si1-xGex / Si(001) surface: A high-resolution electron energy loss spectroscopy study". Surface Science 402; 52-56 (1998).
16. **R. Chelly**, T. Angot, P. Louis, D. Bolmont, J.J. Koulmann "In-situ monitoring of growth rate parameters in Hot-wire assisted GS-MBE using a Quartz Crystal Microbalance" Applied Surface Science 115, 299-306 (1997).
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